

Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, Ča 90638 Phone: (562) 404-4474 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

DESIGNER'S DATA SHEET

Part Number / Ordering Information 1/

SSR10C

 Screening₂/

__ = Not Screened TX = TX Level TXV = TXV Level S = S Level

Package

S.22 = SMD.22

Voltage

50 = 500 V 60 = 600 V

SSR10C50S.22 SSR10C60S.22

10 AMP / 500 – 600 VOLTS SILICON CARBIDE SCHOTTKY RECTIFIER

Features:

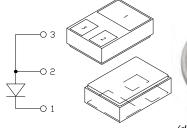
- 500 600 V Silicon Carbide Schottky Rectifier
- New Semiconductor Material
- Switching Behavior Benchmark
- No Reverse Recovery
- No Forward Recovery
- No Switching Time Change Over Temperature
- Hermetic Packages
- TX, TXV, and S-Level Screening Available^{2/}

Maximum Ratings ^{3/}		Symbol	Value	Unit		
Peak Repetitive Reverse and Peak Surge Reverse Voltage	SSR10C50 SSR10C60	V _{RRM} V _{RSM}	500 600	v		
Average Rectified Forward Current (Resistive Load, 60 Hz Sine Wave)		lo	10	Α		
Non Repetitive Peak Surge Current (8.3 ms Pulse, Half Sine Wave)		I _{FSM}	70	Α		
Operating & Storage Temperature		T _{OP} & T _{STG}	-55 to +175	°C		
Maximum Thermal Resistance (Junction to Case)		R _θ Jc	3	°C/W		

Notes: *Pulsed per MIL-STD-750.

- 1/ For ordering information, price, and availability, contact factory.
- 2/ Screening based on MIL-PRF-19500. Screening flows available on request.
- 3/ All electrical characteristics @ 25°C unless otherwise specified.

SMD.22 (S.22)





(dime used for size reference)

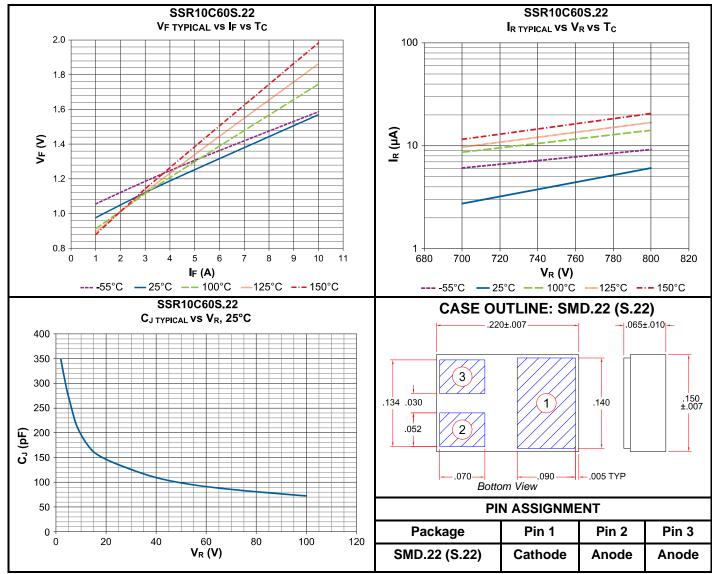


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SSR10C50S.22 SSR10C60S.22

Electrical Characteristic3/		Symbol	Min	Тур	Max	Unit
Instantaneous Forward Voltage Drop (T _J = 25°C, pulsed)	$I_F = 5 A$ $I_F = 10 A$	V_{F1}		1.30 1.70	1.65 1.90	V
Instantaneous Forward Voltage Drop (T _J = 150°C, pulsed)	I _F = 5 A I _F = 10 A	V_{F2}		1.35 1.95	1.75 2.20	V
Reverse Leakage Current (V _R = Rated V _R , T _J = 25°C, pulsed)		I _{R1}		0.1	10	μΑ
Reverse Leakage Current (V _R = Rated V _R , T _J = 100°C, pulsed)		I _{R2}		0.2	20	μΑ
Junction Capacitance (V _R = 10 V _{DC} , T _C = 25°C, f = 1 MHz)		C₁		200	300	рF



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- 3/ All electrical characteristics @ 25°C unless otherwise specified.

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: SH0131A

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